

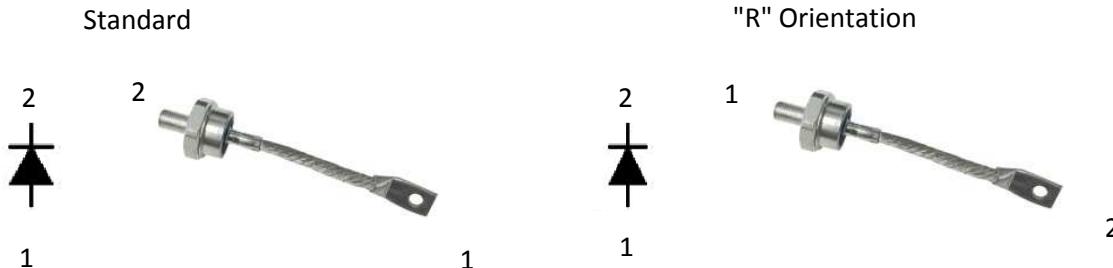
## Silicon Standard Recovery Diode

**$V_{RRM} = 200 \text{ V - } 1400 \text{ V}$**   
 **$I_F = 100 \text{ A}$**

### Features

- High Surge Capability
- Types up to 1400 V  $V_{RRM}$

**DO-8 Package**



**Maximum ratings, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)**

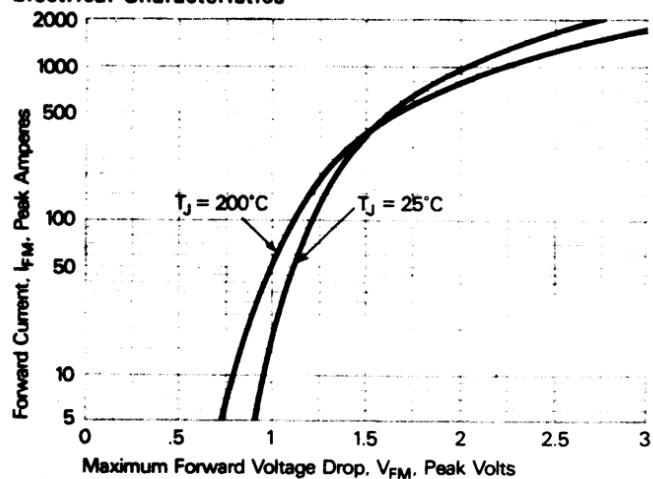
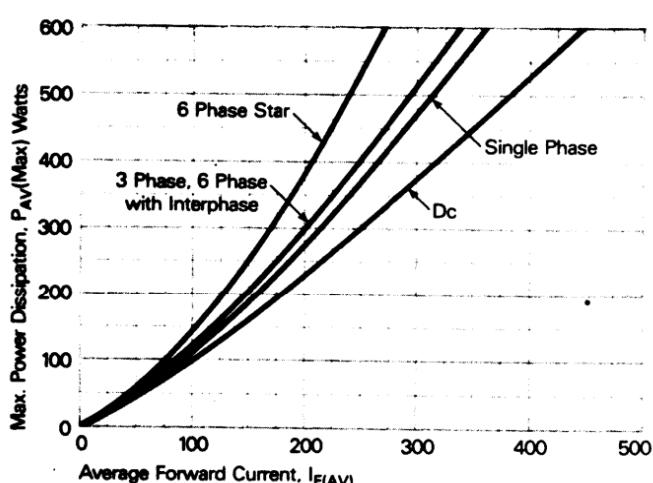
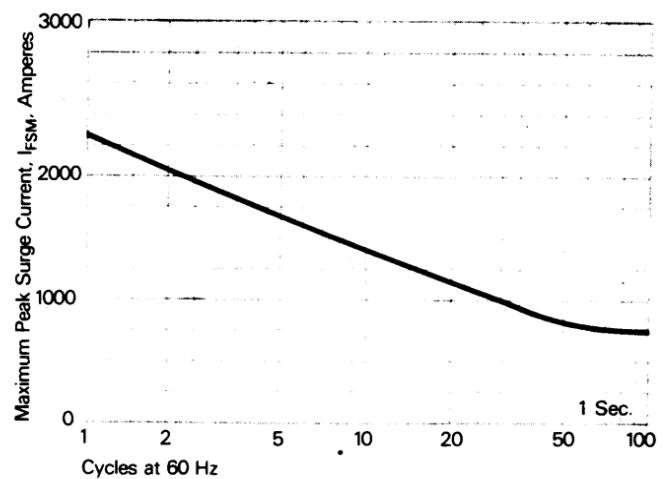
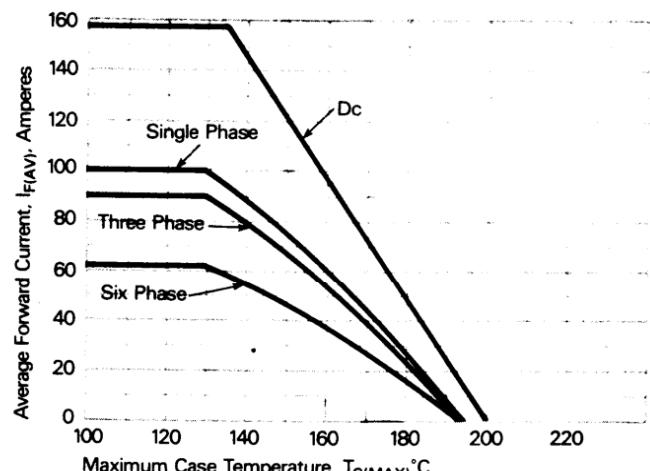
Parameter	Symbol	Conditions	1N3289A(R)	1N3291A(R)	1N3293A(R)	1N3294A(R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		200	400	600	800	V
DC blocking voltage	$V_{DC}$		200	400	600	800	V
Continuous forward current	$I_F$	$T_C \leq 130^\circ\text{C}$	100	100	100	100	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}, t_p = 8.3 \text{ ms}$	2300	2300	2300	2300	A
$I_{2t}$ for fusing	$I_{2t}$	60 Hz Half wave	22000	22000	22000	22000	$\text{A}^2\text{sec}$
Operating temperature	$T_j$		-40 to 200	-40 to 200	-40 to 200	-40 to 200	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-40 to 200	-40 to 200	-40 to 200	-40 to 200	$^\circ\text{C}$

**Electrical characteristics, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	1N3289A(R)	1N3291A(R)	1N3293A(R)	1N3294A(R)	Unit
Diode forward voltage	$V_F$	$I_F = 100 \text{ A}, T_j = 130^\circ\text{C}$	1.5	1.5	1.5	1.5	V
Reverse current	$I_R$	$V_R = V_{RRM}, T_j = 130^\circ\text{C}$	24	24	17	13	mA

### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		0.40	0.40	0.40	0.40	$^\circ\text{C/W}$
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**Electrical Characteristics**

**Figure 1. Forward Current vs. Forward Voltage.**

**Figure 3. Power dissipation vs. Average forward current.**

**Figure 2. Maximum allowable surge current at rated load conditions.**

**Figure 4. Forward Current vs. Case Temperature.**